# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

MMBT3904LP(MS)

Product specification



#### MSKSEMI SEMICONDUCTOR

### Features

- Low profile package
- Ideal for automated placement
- Low saturation voltages
- High voltage capability
- High Stability and High Reliability
- RoHS Compliant

## Applications

- amplifying signal
- Electronic switch
- Oscillating circuit
- Variable resistance
- Lighting applications

## Appearance & Symbol

PACKAGE OUTLINE	Pin Configuration	Marking
1: Base 2: Emitter 3: Collector DFN1006-3	Base Emitter	6P



#### Absolute Maximum Ratings (T=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current Continuous	lc	0.2	A
Power Dissipation	PD	0.3	W
Operating Junction temperature	TJ	-55 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

#### Electrical Characteristics (T=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	V <sub>CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	60			V
Collector-Emitter Breakdown Voltage	V <sub>CER</sub>	I <sub>C</sub> =1mA,I <sub>B</sub> =0	40			V
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>E</sub> =10uA,I <sub>C</sub> =0	6			V
Collector Cut-Off Current	Ісво	V <sub>CB</sub> =60V, I <sub>E</sub> =0			100	nA
Collector Cut-Off Current	ICEX	V <sub>CE</sub> =30V,V <sub>EB(off)</sub> =3V			50	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V,I <sub>C</sub> =0			100	nA
	h <sub>FE</sub>	V <sub>CE</sub> =1V,I <sub>C</sub> =0.1mA	40			
		V <sub>CE</sub> =1V,I <sub>C</sub> =1mA	70			
DC current gain		V <sub>CE</sub> =1V,I <sub>C</sub> =10mA	100		300	
		V <sub>CE</sub> =1V,I <sub>C</sub> =50mA	60			
		V <sub>CE</sub> =1V,I <sub>C</sub> =100mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.3	V
Base -emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{C}$ =50mA, $I_{B}$ =5mA			0.95	V
Transition frequency	fT	V <sub>CE</sub> = 20V, I <sub>C</sub> =10mA,f=100MHz	300			MHZ
Delay Time	td	V <sub>CC</sub> =3V, I <sub>C</sub> = 10mA,		35		
Rise time	tr	$V_{BE(off)}$ =-0.5V, $I_{B1}$ =1mA		35		ns
Storage time	ts	Vcc =3V, Ic =10mA,		200		us
Fall time	tf	$I_{B1} = I_{B2} = 1mA$		50		ns

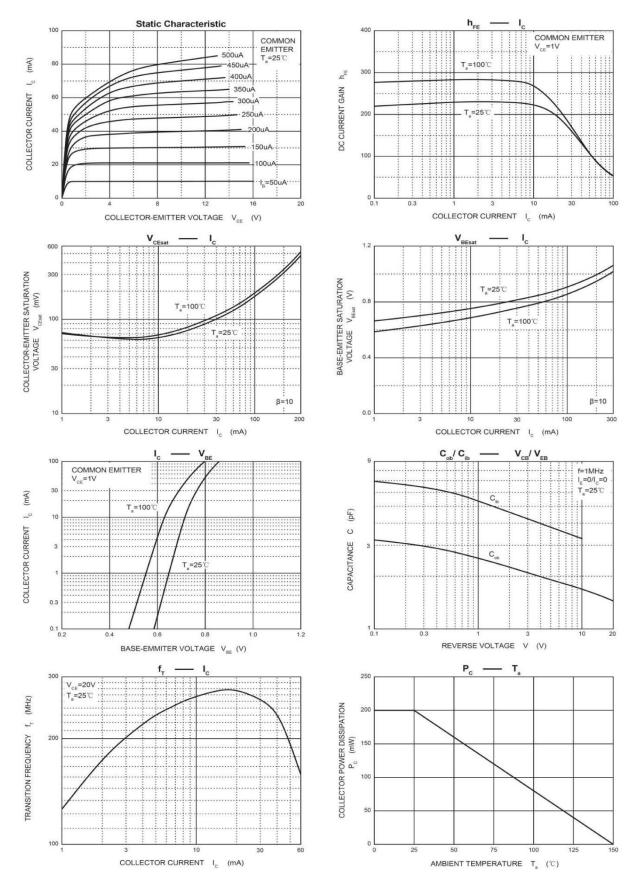
#### Classification of hFE

Range

100-300



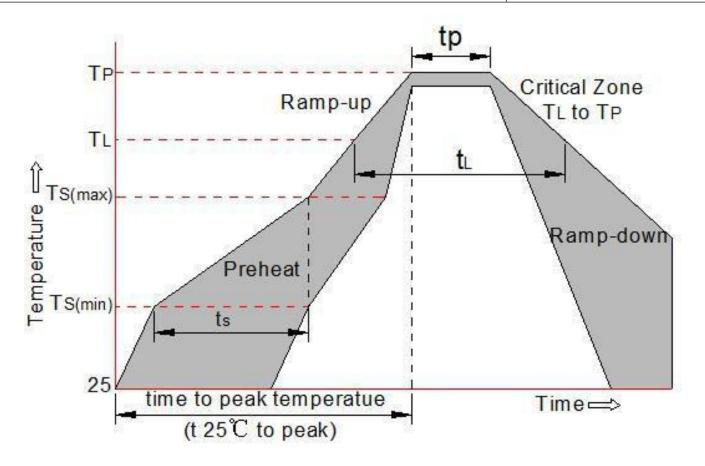
## **Typical Characteristics**





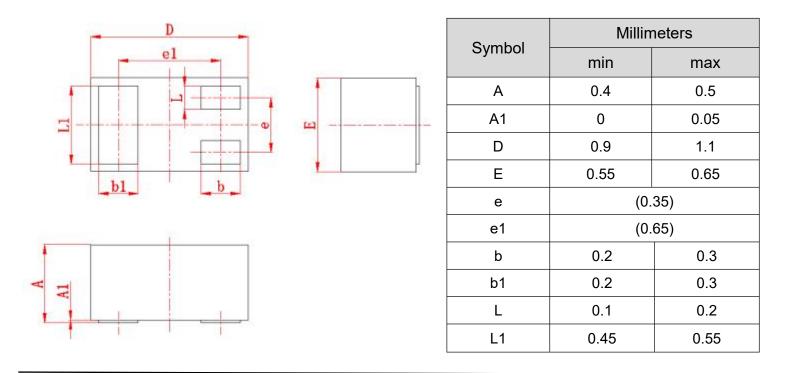
#### Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
	-Temperature Min (T <sub>s(min)</sub> )	+150℃
Pre Heat	-Temperature Max(T <sub>s(max)</sub> )	<b>+200</b> ℃
	-Time (Min to Max) (ts)	60-180 secs.
Average	Average ramp up rate (Liquid us Temp (T∟) to peak)	
	$T_{s(max)}$ to $T_L$ - Ramp-up Rate	
	-Temperature(T <sub>L</sub> ) (Liquid us)	+217℃
Reflow	-Temperature(t <sub>∟</sub> )	60-150 secs.
Peak Temp (T <sub>p</sub> )		<b>+260(+0/-5)</b> ℃
Time within 5 $^\circ \!$		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25 $^\circ \mathbb{C}$ to Peak Temp (T <sub>P</sub> )		8 min. Max
Do not exceed		+260℃

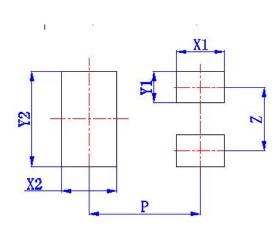




#### Package mechanical data



### Suggested Land Pattern



Symbol	Dimension in Millimeters	
Cymbol	typ	
X1	(0.3)	
X2	(0.35)	
Y1	(0.2)	
Y2	(0.6)	
Z	(0.4)	
Р	(0.7)	

## **REEL SPECIFICATION**

P/N	PKG	QTY
MMBT3904LP(MS)	DFN1006-3	10000



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